

SGF80N60UF

Ultra-Fast IGBT

General Description

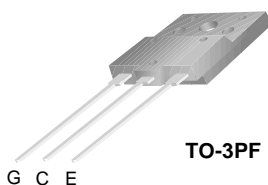
Fairchild's Insulated Gate Bipolar Transistor(IGBT) UF series provides low conduction and switching losses. UF series is designed for the applications such as motor control and general inverters where High Speed Switching is required.

Features

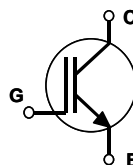
- High Speed Switching
- Low Saturation Voltage : $V_{CE(sat)} = 2.1\text{ V @ } I_C = 40\text{ A}$
- High Input Impedance

Application

AC & DC Motor controls, General Purpose Inverters, Robotics, Servo Controls



TO-3PF



Absolute Maximum Ratings T_C = 25°C unless otherwise noted

Symbol	Description	SGF80N60UF	Units
V _{CES}	Collector-Emitter Voltage	600	V
V _{GES}	Gate-Emitter Voltage	± 20	V
I _C	Collector Current @ T _C = 25°C	80	A
	Collector Current @ T _C = 100°C	40	A
I _{CM(1)}	Pulsed Collector Current	220	A
P _D	Maximum Power Dissipation @ T _C = 25°C	110	W
	Maximum Power Dissipation @ T _C = 100°C	45	W
T _J	Operating Junction Temperature	-55 to +150	°C
T _{stg}	Storage Temperature Range	-55 to +150	°C
T _L	Maximum Lead Temp. for Soldering Purposes, 1/8" from Case for 5 Seconds	300	°C

Notes :

(1) Repetitive rating : Pulse width limited by max. junction temperature

Thermal Characteristics

Symbol	Parameter	Typ.	Max.	Units
R _{θJC}	Thermal Resistance, Junction-to-Case	--	1.1	°C/W
R _{θJA}	Thermal Resistance, Junction-to-Ambient	--	40	°C/W

Electrical Characteristics of IGBT $T_C = 25^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
Off Characteristics						
BV_{CES}	Collector-Emitter Breakdown Voltage	$V_{GE} = 0V, I_C = 250\mu A$	600	--	--	V
$\frac{\Delta BV_{CES}}{\Delta T_J}$	Temperature Coeff. of Breakdown Voltage	$V_{GE} = 0V, I_C = 1mA$	--	0.6	--	$V/^\circ C$
I_{CES}	Collector Cut-Off Current	$V_{CE} = V_{CES}, V_{GE} = 0V$	--	--	250	μA
I_{GES}	G-E Leakage Current	$V_{GE} = V_{GES}, V_{CE} = 0V$	--	--	± 100	nA
On Characteristics						
$V_{GE(th)}$	G-E Threshold Voltage	$I_C = 40mA, V_{CE} = V_{GE}$	3.5	4.5	6.5	V
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C = 40A, V_{GE} = 15V$	--	2.1	2.6	V
		$I_C = 80A, V_{GE} = 15V$	--	2.6	--	V
Dynamic Characteristics						
C_{ies}	Input Capacitance	$V_{CE} = 30V, V_{GE} = 0V,$ $f = 1MHz$	--	2790	--	pF
C_{oes}	Output Capacitance		--	350	--	pF
C_{res}	Reverse Transfer Capacitance		--	100	--	pF
Switching Characteristics						
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 25^\circ C$	--	23	--	ns
t_r	Rise Time		--	50	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	90	130	ns
t_f	Fall Time		--	50	150	ns
E_{on}	Turn-On Switching Loss		--	570	--	μJ
E_{off}	Turn-Off Switching Loss		--	590	--	μJ
E_{ts}	Total Switching Loss	--	1160	1500	μJ	
$t_{d(on)}$	Turn-On Delay Time	$V_{CC} = 300V, I_C = 40A,$ $R_G = 5\Omega, V_{GE} = 15V,$ Inductive Load, $T_C = 125^\circ C$	--	30	--	ns
t_r	Rise Time		--	55	--	ns
$t_{d(off)}$	Turn-Off Delay Time		--	150	200	ns
t_f	Fall Time		--	160	250	ns
E_{on}	Turn- On Switching Loss		--	630	--	μJ
E_{off}	Turn- Off Switching Loss		--	940	--	μJ
E_{ts}	Total Switching Loss	--	1580	2000	μJ	
Q_g	Total Gate Charge	$V_{CE} = 300V, I_C = 40A,$ $V_{GE} = 15V$	--	175	250	nC
Q_{ge}	Gate-Emitter Charge		--	25	40	nC
Q_{gc}	Gate-Collector Charge		--	60	90	nC
L_e	Internal Emitter Inductance	Measured 5mm from PKG	--	14	--	nH

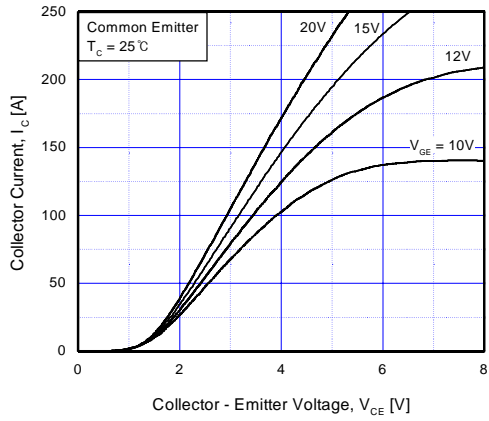


Fig 1. Typical Output Characteristics

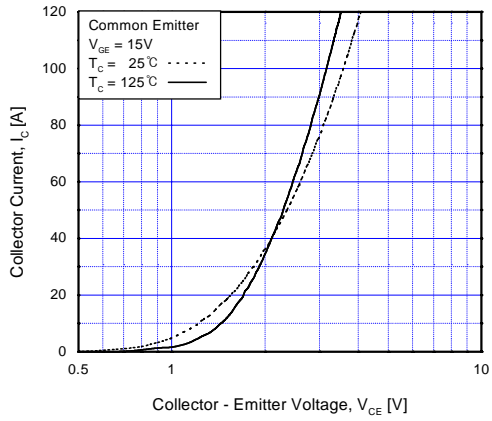


Fig 2. Typical Saturation Voltage Characteristics

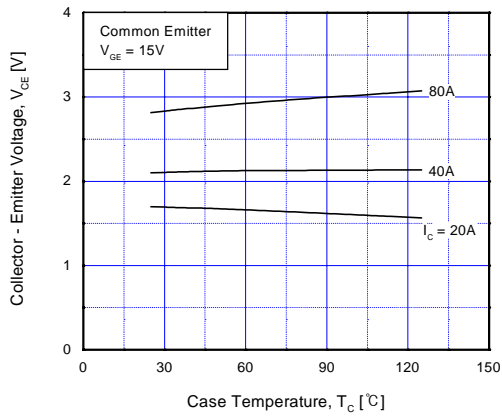


Fig 3. Saturation Voltage vs. Case Temperature at Variant Current Level

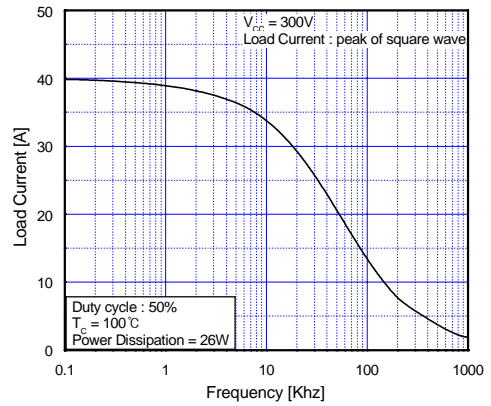


Fig 4. Load Current vs. Frequency

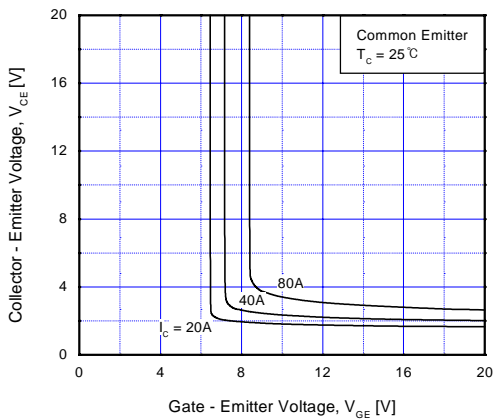


Fig 5. Saturation Voltage vs. V_{GE}

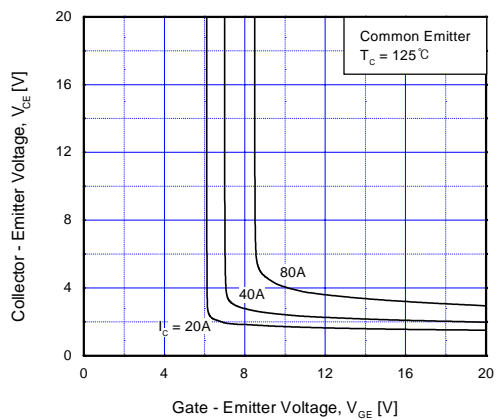


Fig 6. Saturation Voltage vs. V_{GE}

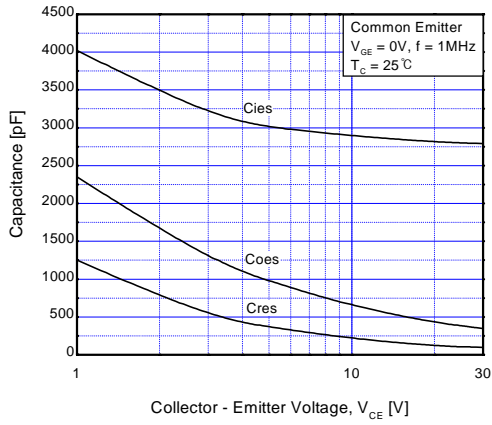


Fig 7. Capacitance Characteristics

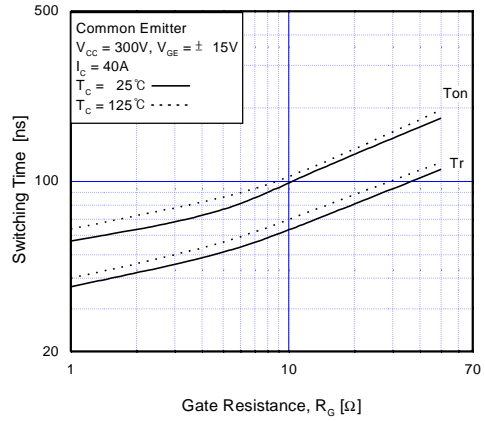


Fig 8. Turn-On Characteristics vs. Gate Resistance

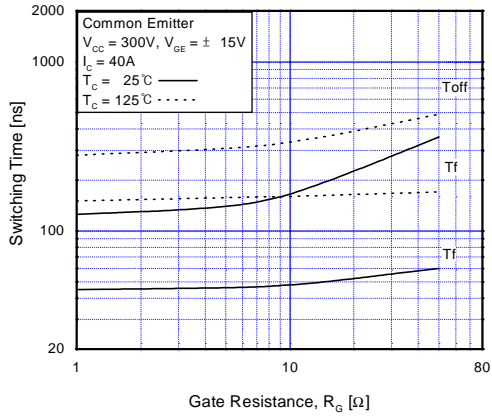


Fig 9. Turn-Off Characteristics vs. Gate Resistance

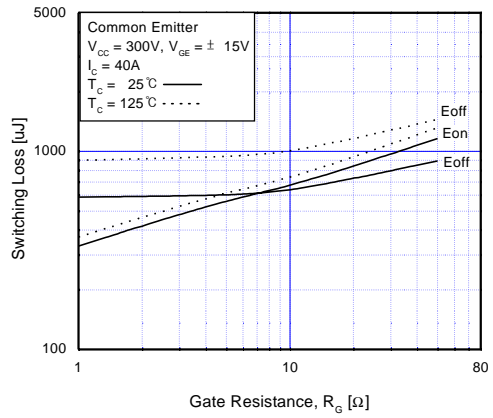


Fig 10. Switching Loss vs. Gate Resistance

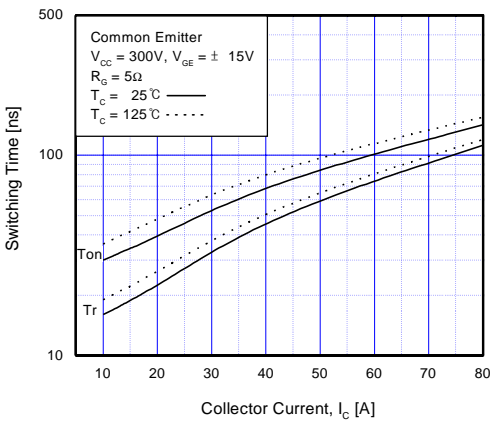


Fig 11. Turn-On Characteristics vs. Collector Current

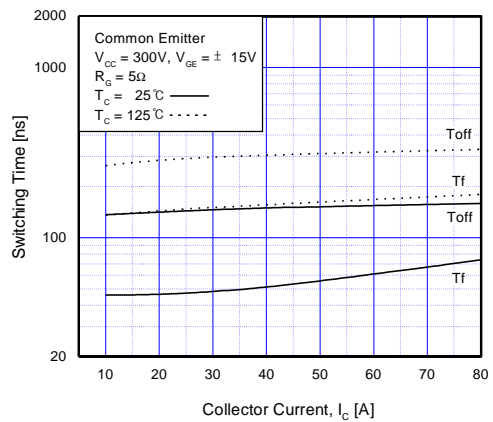


Fig 12. Turn-Off Characteristics vs. Collector Current

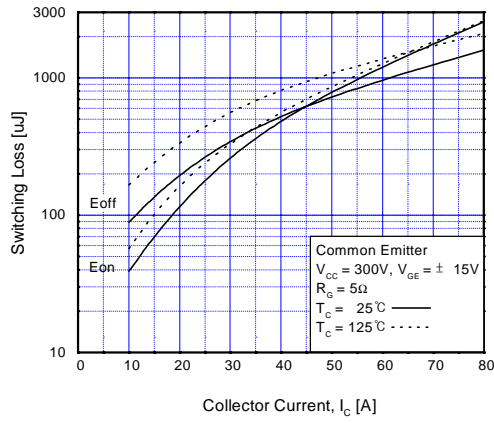


Fig 13. Switching Loss vs. Collector Current

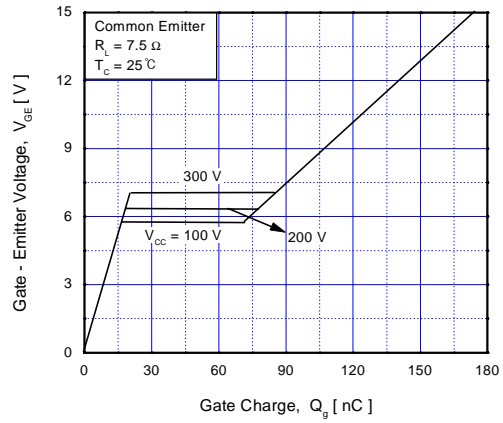


Fig 14. Gate Charge Characteristics

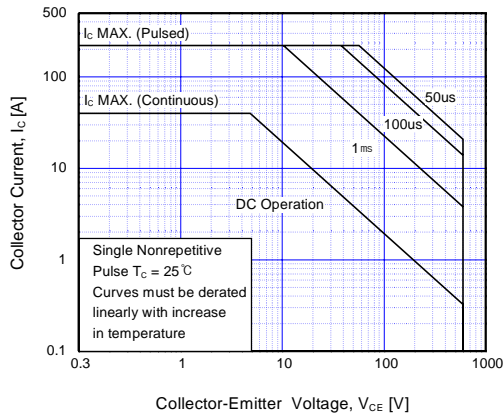


Fig 15. SOA Characteristics

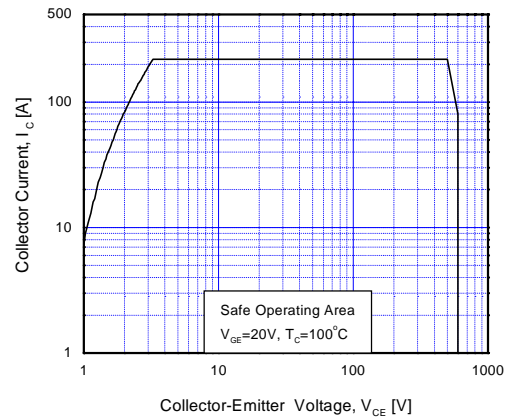


Fig 16. Turn-Off SOA Characteristics

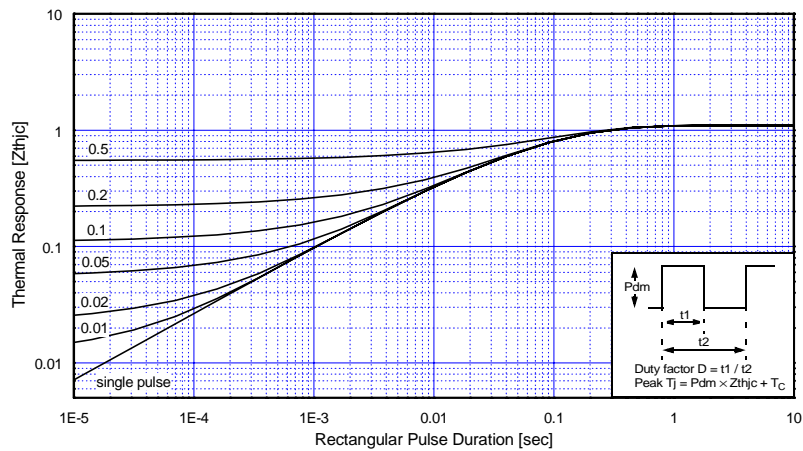
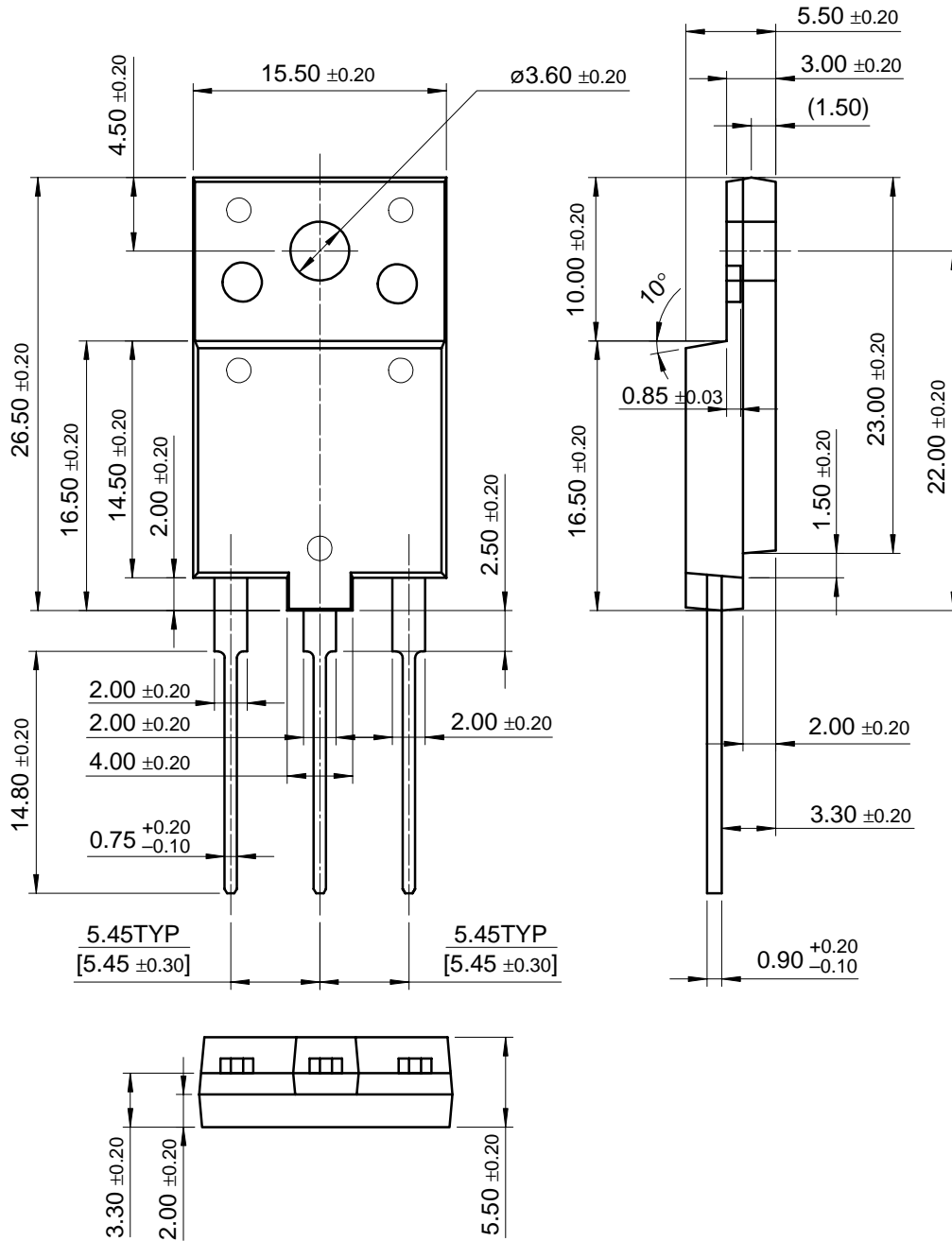


Fig 17. Transient Thermal Impedance of IGBT

Package Dimension

TO-3PF

SGF80N60UF



Dimensions in Millimeters

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